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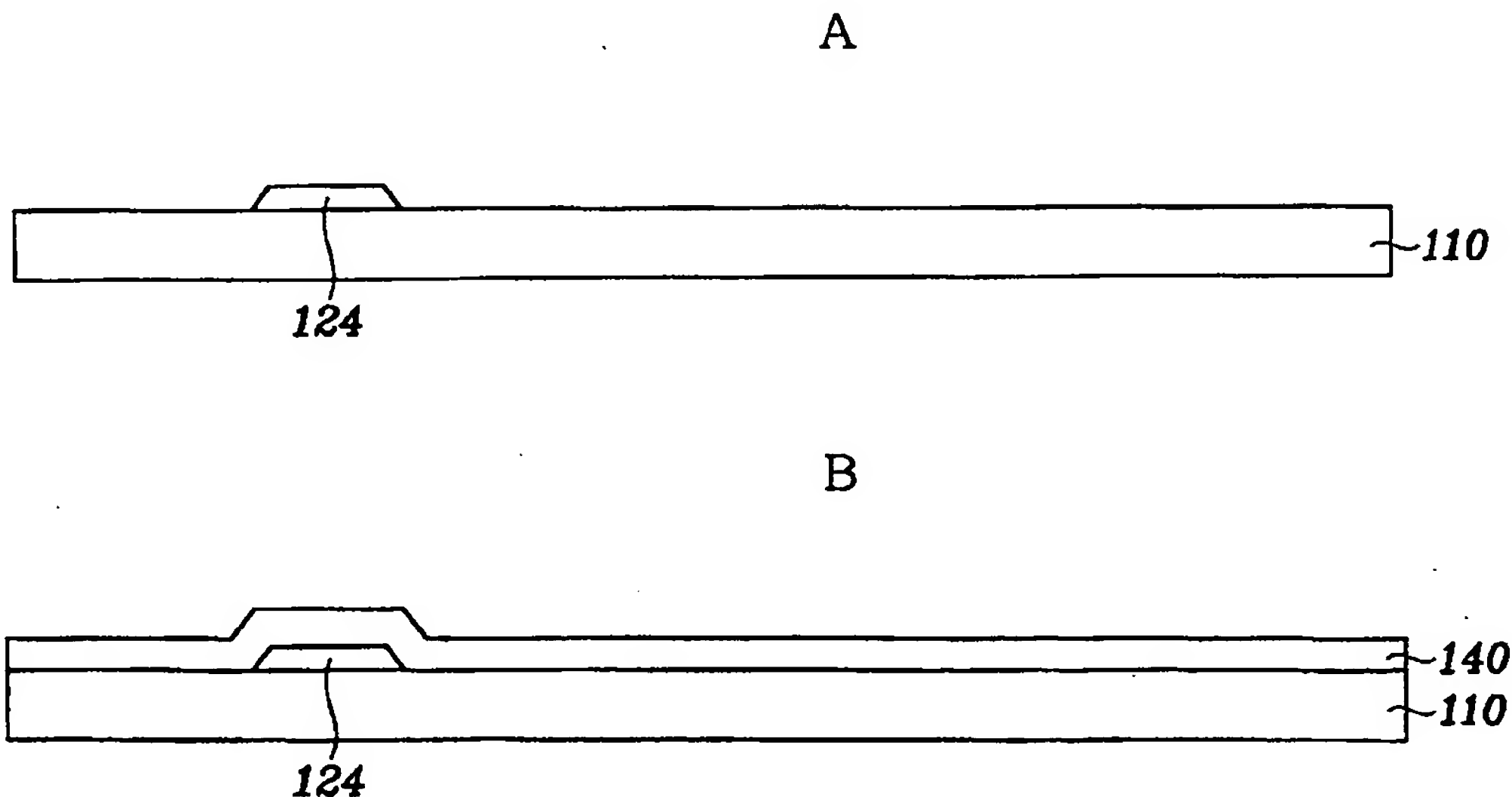
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(54) Title: **THIN FILM TRANSISTOR ARRAY PANEL AND MANUFACTURING METHOD THEREOF**



(57) Abstract: The present invention provides a thin film transistor comprising: a substrate (110); a gate electrode (124) formed on the substrate; a gate insulating layer (140) covering the substrate and the gate electrode; a source electrode and a drain electrode (173, 175) formed on the gate insulating layer; a semiconductor layer (150) formed on the gate insulating layer, the source electrode and the drain electrode; and a passivation layer (180) covering the semiconductor layer, the source electrode, the drain electrode and the gate insulating layer, wherein at least one of the gate insulating layer and the passivation layer is made of Parylene.



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